

Title (en)

Half mirror film producing method and optical element comprising a half mirror film

Title (de)

Verfahren zur Herstellung eines halbdurchlässigen Spiegelfilms und diesen beinhaltende optische Elemente

Title (fr)

Procédé de fabrication d'un film semi-réfléchissant et élément optique avec un film semi-réfléchissant

Publication

EP 1286184 A3 20040428 (EN)

Application

EP 02016965 A 20020801

Priority

JP 2001239011 A 20010807

Abstract (en)

[origin: EP1286184A2] A method of producing a half mirror film on a substrate having a light transmissive property, comprising steps of: electrically discharging between electrodes facing each other under an atmospheric pressure or an approximate atmospheric pressure so as to make an reactive gas on a plasma state; and exposing a substrate to the reactive gas on the plasma state so as to form a half mirror film on the substrate.
<IMAGE>

IPC 1-7

G02B 1/10; **C03C 1/00**; **G02B 5/08**; **C03C 17/34**; **C23C 16/40**; **C23C 16/54**; **C23C 16/50**; **G02B 27/14**; **C23C 16/02**

IPC 8 full level

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CPC (source: EP KR US)

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Citation (search report)

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DOCDB simple family (application)

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